风光欣技术资料

RN1304

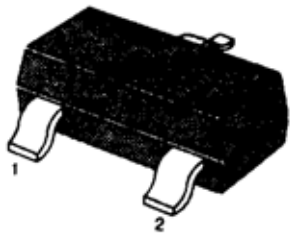
—NPN silicon —

■■**APPLICATION**：Interface Circuit and Driver Circuit Applications.

SOT-323

■■**MAXIMUM RATINGS** (Ta＝25℃)

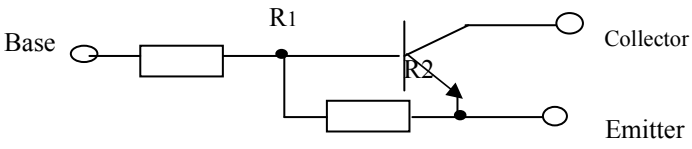
PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	10	V
Collector current	I_C	100	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

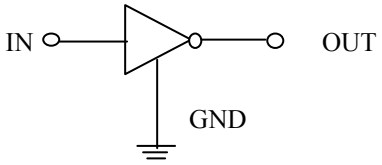


1.Base 2 .Emitter 3 .Collector

■■**ELECTRICAL CHARACTERISTICS**（**Ta=25℃**）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	80				V_{CE}= 5V，I_C= 10mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 50V，I_E=0
Collector-Emitter Cut-off Current	I_{CEO}			0.5	μA	V_{CB}= 50V，I_E=0
Emitter Cut-off Current	I_{EBO}	0.082		0.15	mA	V_{EB}= 10V，I_C=0
Input Voltage（ON）	$V_{I(ON)}$	1.5		5	V	V_{CE}= 0.2V，I_C= 5mA
Output Voltage（OFF）	$V_{I(OFF)}$	1		1.5	V	V_{CE}= 5V，I_C= 0.1mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.1	0.3	V	I_C= 5mA，I_B= 0.25mA
Gain bandwidth product	f_T	100	250		MHz	I_C= 5mA，V_{CE}= 10V
Base Resistance	R_1	32.9	47	61.1	KΩ	
Emitter Resistance	R_2	32.9	47	61.1		
Common Base Output Capacitance	C_{ob}		3	6	pF	V_{CB}= 10V, I_E=0, f = 1MHz





■■h_{FE} **Classification And Marking**

Print Mark	XD
Classification	
h_{FE}	≥80